ABSTRACT OF THE DISCLOSURE

GROUP III-V COMPOUND SEMICONDUCTOR AND METHOD OF PRODUCING THE SAME

Provided is a method of producing a group III-V compound semiconductor having a low dislocation density without increasing the thickness of a re-grown layer, the method includes a re-growing process using a mask pattern, and threading dislocations in the re-grown layer are terminated by the voids formed on the pattern.

(Figure 3)

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